

# Product data sheet

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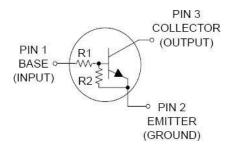


#### Features:

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

SOT-523

#### **Electrical Symbol:**



Symbol	Parameter	Value	Units
V <sub>сво</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
lc	Collector Current	100	mA
PD	Power Dissipation	150	mW
R <sub>0JA</sub>	Thermal Resistance from Junction to Ambient	600	°C /W
$T_J T_{STG}$	Junction & Storage Temperature Range	-55 to +150	°C

These ratings are limiting values above which the serviceability of the device may be impaired.





#### **Device Marking & Resistor Values:**

P/N	Mark	R1 (KΩ)	R2 (KΩ)
DTC114EE-MS	24	10	10
DTC124EE-MS	25	22	22
DTC144EE-MS	26	47	47
DTC114YE-MS	64	10	47
DTC114TE-MS	04	10	$\infty$
DTC143TE-MS	03	4.7	$\infty$
DTC123EE-MS	22	2.2	2.2
DTC143EE-MS	23	4.7	4.7
DTC143ZE-MS	E23	4.7	47
DTC124XE-MS	45	22	47
DTC123JE-MS	E42	2.2	47

#### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

#### **Off Characteristics**

Cumb al	Parameter	Test Condition	Limits			11
Symbol	Farameter		Min	Тур	Мах	Unit
Ісво	Collector-Base Cutoff Current	V <sub>CB</sub> =50V, I <sub>E</sub> =0A	-	-	100	nA
ICEO	Collector-Emitter Cutoff Current	V <sub>CE</sub> =50V, I <sub>B</sub> =0A	-	-	500	nA
I <sub>EBO</sub>	Emitter-Base Cutoff Current	V <sub>EB</sub> =6.0V, I <sub>C</sub> =0A				
	DTC114EE-MS		-	-	0.50	
	DTC124EE-MS		-	-	0.20	
	DTC144EE-MS		-	-	0.10	
	DTC114YE-MS		-	-	0.20	
	DTC114TE-MS		-	-	0.90	
	DTC143TE-MS		-	-	1.90	mA
	DTC123EE-MS		-	-	2.30	
	DTC143EE-MS		-	-	1.50	
	DTC143ZE-MS		-	-	0.18	
	DTC124XE-MS		-	-	0.13	
	DTC123JE-MS		-	-	0.20	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I <sub>C</sub> =10uA, I <sub>E</sub> =0A	50	-	-	Volts
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage (Note 1)	I <sub>C</sub> =2.0mA, I <sub>B</sub> =0A	50	-	-	Volts

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%)





Symbol	Parameter	Test Condition	Limits			Unit	
Symbol	Parameter	Test Condition	Min	Тур	Max		
H <sub>FE</sub>	DC Current Dain	$V_{CE}$ =10V, $I_C$ =5.0mA					
	DTC114EE-MS		35	60			
	DTC124EE-MS		60	100			
	DTC144EE-MS		80	140			
	DTC114YE-MS		80	140			
	DTC114TE-MS		160	350			
	DTC143TE-MS		160	350			
	DTC123EE-MS		8.0	15			
	DTC143EE-MS		15	30			
	DTC143ZE-MS		80	200			
	DTC124XE-MS		80	150			
	DTC123JE-MS		80	140			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage						
	DTC114EE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =0.3mA					
	DTC124EE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =0.3mA					
	DTC144EE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =0.3mA					
	DTC114YE-MS	Ic=10mA, I <sub>B</sub> =0.3mA					
	DTC114TE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.25	Volts	
	DTC143TE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.25	VOILS	
	DTC123EE-MS	Ic=10mA, I <sub>B</sub> =5mA					
	DTC143EE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA					
	DTC143ZE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA					
	DTC124XE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA					
	DTC123JE-MS	I <sub>C</sub> =10mA, I <sub>B</sub> =0.3mA					
VoL	Output Voltage (on)	R <sub>L</sub> = 1.0KΩ					
	DTC114EE-MS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V					
	DTC124EE-MS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V					
	DTC144EE-MS	$V_{CC}$ =5.0V, $V_{B}$ =3.5V					
	DTC114YE-MS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V					
	DTC114TE-MS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V			0.20	Volts	
	DTC143TE-MS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V			0.20	VOILS	
	DTC123EEMS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V					
	DTC143EEMS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V					
	DTC143ZEMS	V <sub>CC</sub> =5.0V, V <sub>B</sub> =2.5V					
	DTC124XEMS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V					
	DTC123JEMS	$V_{CC}$ =5.0V, $V_{B}$ =2.5V					





#### **On Characteristics**

Symbol	Parameter	Test Condition	Limits		Unit	
Symbol	Farameter	Test Condition	Min	Тур	Max	Unit
V <sub>он</sub>	Output Voltage (on)	R∟= 1.0KΩ				
	DTC114EE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.5V				
	DTC124EE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.5V				
	DTC144EE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.5V				
	DTC114YE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.5V				
	DTC114TE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.25V	4.9			Volts
	DTC143TE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.25V	4.9			VOILS
	DTC123EE-MS	V <sub>CC</sub> =5.0V, V <sub>B</sub> =0.5V				
	DTC143EE-MS	V <sub>CC</sub> =5.0V, V <sub>B</sub> =0.5V				
	DTC143ZE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.25V				
	DTC124XE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.5V				
	DTC123JE-MS	$V_{CC}$ =5.0V, $V_{B}$ =0.5V				

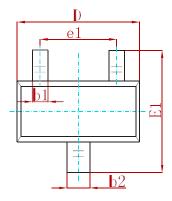
## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

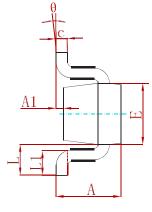
Symbol	Chara	acteristic	Min	Тур	Max	Uni
R1	Input Resistor	DTC114EEMS	7.0	10	13	<u> </u>
		DTC124EE-MS	15.4	22	28.6	
		DTC144EE-MS	32.9	47	61.1	
		DTC114YE-MS	7.0	10	13	
		DTC114TE-MS	7.0	10	13	
		DTC143TE-MS	3.3	4.7	6.1	KΩ
		DTC123EE-MS	1.5	2.2	2.9	
		DTC143EE-MS	3.3	4.7	6.1	
		DTC143ZE-MS	3.3	4.7	6.1	
		DTC124XE-MS	15.4	22	28.6	
		DTC123JE-MS	1.54	2.2	2.86	
R1/R2	Resistor Ratio	DTC114EE-MS	0.8	1.0	1.2	
		DTC124EE-MS	0.8	1.0	1.2	
		DTC144EE-MS	0.8	1.0	1.2	
		DTC114YE-MS	0.17	0.21	0.25	
		DTC114TE-MS	-	-	-	
		DTC143TE-MS	-	-	-	
		DTC123EE-MS	0.8	1.0	1.2	
		DTC143EE-MS	0.8	1.0	1.2	
		DTC143ZE-MS	0.055	0.1	0.185	
		DTC124XE-MS	0.38	0.47	0.56	
		DTC123JE-MS	0.038	0.047	0.056	

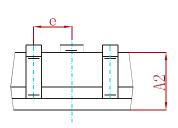


DTCXXXX-MS

## PACKAGE MECHANICAL DATA

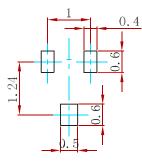






Symbol	Dimensions	In Millimeters	Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
С	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500	TYP.	0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016	REF.
L1	0.260	0.460	0.010	0.018
0	0°	8°	0°	8°

## Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
DTCXXXXX-MS	SOT-523	3000





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